Sub D1

7. (Newly Added) A method for manufacturing a bottom gate-type thin-film transistor on a transparent insulating substrate, comprising the steps of:

forming a gate electrode on a transparent substrate;

forming a gate insulating film on said gate electrode;

forming a semiconductor layer on said gate insulating film;

forming a mask on said semiconductor layer corresponding to said gate electrode;

doping impurities selectively into said semiconductor layer, using said mask;

thoroughly removing the mask used in the doping so that no layer having an impurity density of 10^{13} atoms/cc or greater remain on the semiconductor layer; and

A3 cont'd.

forming an interlayer insulating film on said semiconductor layer, after removal of said mask.

8. (Newly Added) A method defined in Claim 7, further comprising the steps of:

removing, after removal of said mask, residue of said mask, together with a native oxide film formed on said semiconductor layer before formation of said mask.

9. (Newly Added) A method defined in Claim 8, wherein removing said native oxide film by a dilute hydrofluoric acid.

10. (Newly Added) A method defined in Claim 7, wherein the mask of at least some of a plurality of thin film transistors is shorter than the gate electrode in a channel length direction, and a region doped with impurities in the semiconductor layer thereof overlaps the gate electrode.